

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

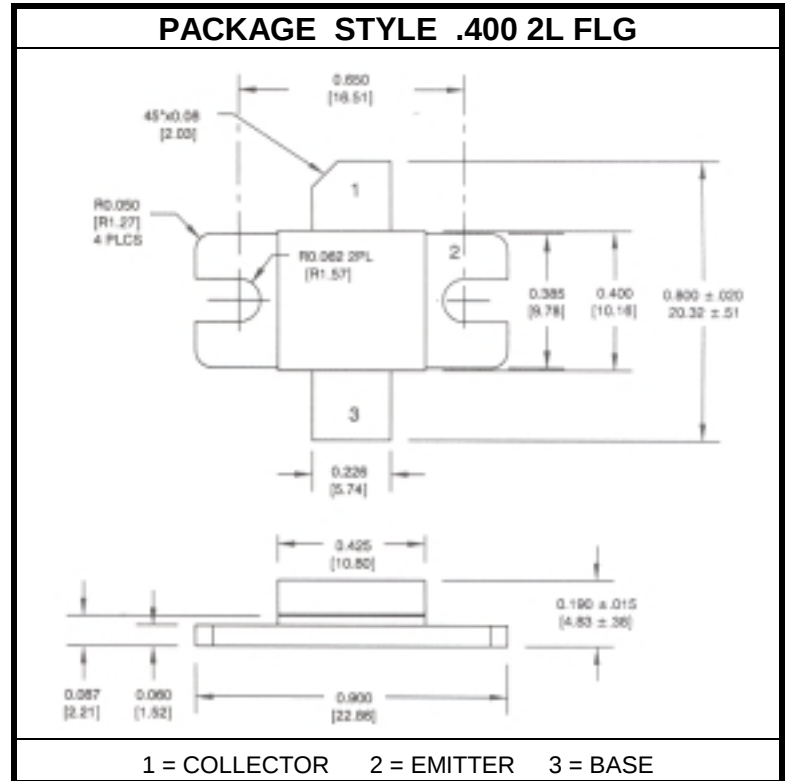
The **ASI PTB20111** is Designed for General Purpose Class AB Power Amplifier Applications up to 900 MHz.

FEATURES:

- 25 W, 860-900 MHz
- Silicon Nitride Passivated
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CBO}	65 V
P_{DISS}	159 W @ $T_C = 25^\circ C$
T_J	$-40^\circ C$ to $+150^\circ C$
T_{STG}	$-40^\circ C$ to $+150^\circ C$
θ_{JC}	1.1 $^\circ C/W$



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100 \text{ mA}$			25			V
BV_{CES}	$I_C = 100 \text{ mA}$			55			V
BV_{EBO}	$I_E = 5.0 \text{ mA}$			3.5			V
h_{FE}	$V_{CE} = 5.0 \text{ V}$	$I_C = 1.0 \text{ A}$		20		100	---
P_G	$V_{CC} = 25 \text{ V}$	$P_{OUT} = 85 \text{ W}$	$f = 900 \text{ MHz}$	8.5	9.5		dB
η_c	$I_{CQ} = 200 \text{ mA}$			50			%
Ψ	$V_{CC} = 25 \text{ V}$	$P_{OUT} = 60 \text{ W}$	$f = 900 \text{ MHz}$			10:1	---
	$I_{CQ} = 200 \text{ mA}$						